

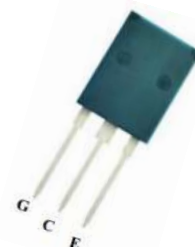
1200V 75A Trench and Field Stop IGBT

DESCRIPTION :

- High ruggedness performance
- Low collector to emitter saturation voltage
- Easy parallel switching capability
- Short circuit withstands time 10μs
- RoHS compliant.

TYPICAL APPLICATIONS :

- Inverter
- Servo drive



TO-247PLUS

IGBT

MAXIMUM RATINGS (Tvj=25°C unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Collector-Emitter Voltage		V_{CES}	1200	V
Continuous collector current	Tc=25°C Tc=100°C	I_C	150 75	A
Pulsed collector current	t _p limited by Tvjmax	I_{CM}	300	A
Gate emitter voltage		V_{GES}	±20	V
Power dissipation	Tc=25°C Tc=100°C	P_{tot}	882 441	W
Operating junction temperature range		Tvj	-40~+175	°C
Storage temperature		T _{STG}	-55~+150	°C

THERMAL CHARACTERISTICS

Characteristic	Condition	Symbol	Max.	Unit
IGBT thermal resistance, junction - case		$R_{th(j-C)}$	0.17	K/W
Diode thermal resistance, junction - case		$R_{th(j-C)}$	0.35	K/W
Thermal resistance, junction - ambient		$R_{th(j-A)}$	40	K/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector-emitter breakdown voltage VGE=0V, IC=250uA Tvj=25°C	BV _{CES}	1200			V
Collector-emitter cut-off current VCE=1200V, VGE=0V Tvj=25°C	I _{CES}			100	uA
Gate-emitter leakage current VCE=0V, VGE=±20V Tvj=25°C	I _{GES}			±100	nA
Gate-Emitter threshold voltage IC=1.0mA, VGE= VCE Tvj=25°C	V _{GE(th)}	5.0	5.5	6.0	V
Collector-Emitter saturation voltage VGE=15V, IC=75A Tvj=25°C VGE=15V, IC=75A Tvj=175°C	V _{CE(SAT)}		1.7 2.2		V
Input capacitance f=1MHz, VCE=30 V, VGE=0 V Tvj=25°C	C _{ies}		6800		pF
Output capacitance f=1MHz, VCE=30 V, VGE=0 V Tvj=25°C	C _{oes}		350		pF
Reverse transfer capacitance f=1MHz, VCE=30 V, VGE=0 V Tvj=25°C	C _{res}		60		pF
Gate charge IC = 75A, VGE = 15 V, VCC =960V Tvj=25°C	Q _G		420		nC
Turn-on delay time IC=75A, VCC=600 V Tvj=25°C VGE=0/15 V, RG=10Ω Tvj=175°C (inductive load)	td _(ON)		86 84		ns
Rise time IC=75A, VCC=600 V Tvj=25°C VGE=0/15 V, RG=10Ω Tvj=175°C (inductive load)	tr		186 194		ns
Turn-off delay time IC=75A, VCC=600 V Tvj=25°C VGE=0/15 V, RG=10Ω Tvj=175°C (inductive load)	td _(OFF)		520 580		ns
Fall time IC=75A, VCC=600 V Tvj=25°C VGE=0/15 V, RG=10Ω Tvj=175°C (inductive load)	tf		84 63		ns

Turn-on energy IC=75A, VCC=600 V VGE=0/15 V, RG=10Ω (inductive load)	Tvj=25°C Tvj=175°C	$E_{(ON)}$	11.9 17.5		mJ
Turn-off energy loss per pulse IC=75A, VCC=600 V VGE=0/15 V, RG=10Ω (inductive load)	Tvj=25°C Tvj=175°C	$E_{(OFF)}$	4.7 6.8		mJ

Diode

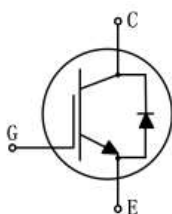
MAXIMUM RATINGS (Tvj=25°C unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Continuous forward current	Tc=100°C	I_F	75	A
Diode maximum current	t _p limited by Tvj max	I_{FM}	150	A

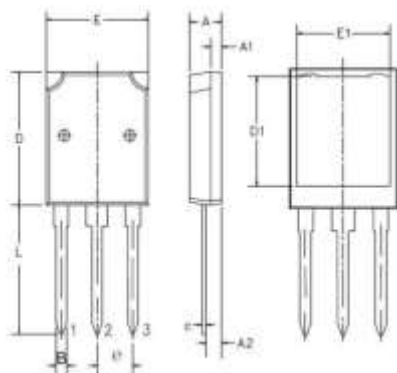
ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Forward voltage IF=75A, Tvj=25°C IF=75A, Tvj=175°C	V_F		1.8 1.5		V
Reverse Recovered Time IF=75 A, -diF/dt =200A/μs VR=600 V	T_{rr}		364 576		ns
Peak reverse recovery current IF=75 A, -diF/dt =200A/μs VR=600 V	I_{RRM}		11 23		A
Reverse Recovered charge IF=75 A, -diF/dt =200A/μs VR=600 V	Q_{rr}		2300 8300		nC

- Circuit diagram



- Package outlines : Dimensions in (mm)



Ref.	Min.(mm)	Typ.(mm)	Max.(mm)
A	4.92	5.00	5.08
A1	2.27	2.35	2.43
A2	1.92	2.00	2.08
B	1.16	1.20	1.24
C	0.58	0.60	0.62
D	20.80	20.90	21.00
E	15.80	15.90	16.00
E1	13.94	14.02	14.10
e	5.34	5.44	5.54
L	19.80	20.00	20.20